

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

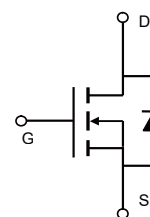
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

- $V_{DS} = 120V, I_D = 70A$
 $R_{DS(ON)} = 8.5m\Omega$, typical (TO-220) @ $V_{GS} = 10V$
 $R_{DS(ON)} = 8.2m\Omega$, typical (TO-263) @ $V_{GS} = 10V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating



TO-220



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VST12N080	VST12N080-TC	TO-220	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	120	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	70	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D (100^\circ C)$	50	A
Pulsed Drain Current	I_{DM}	280	A
Maximum Power Dissipation	P_D	120	W
Derating factor		0.8	W/ $^\circ C$
Single pulse avalanche energy (Note 4)	E_{AS}	352	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.25	$^\circ C/W$
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Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	120		-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =120V, V _{GS} =0V	-	-	1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.0	3.0	4.0	V	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =35A	TO-220	-	8.5	10.0	mΩ
			TO-263		8.2	10.0	
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =35A		60	-	S	
Dynamic Characteristics (Note3)							
Input Capacitance	C _{iss}	V _{DS} =60V, V _{GS} =0V, F=1.0MHz	-	3050	-	pF	
Output Capacitance	C _{oss}		-	280	-	pF	
Reverse Transfer Capacitance	C _{rss}		-	22	-	pF	
Switching Characteristics (Note 3)							
Turn-on Delay Time	t _{d(on)}	V _{DD} =60V, I _D =35A V _{GS} =10V, R _G =1.6Ω	-	15	-	nS	
Turn-on Rise Time	t _r		-	10	-	nS	
Turn-Off Delay Time	t _{d(off)}		-	34	-	nS	
Turn-Off Fall Time	t _f		-	8	-	nS	
Total Gate Charge	Q _g	V _{DS} =60V, I _D =35A, V _{GS} =10V	-	53	-	nC	
Gate-Source Charge	Q _{gs}		-	20	-	nC	
Gate-Drain Charge	Q _{gd}		-	12.5	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 2)	V _{SD}	V _{GS} =0V, I _S =35A	-	-	1.2	V	
Diode Forward Current	I _S		-	-	70	A	
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 35A di/dt = 100A/μs (Note3)	-	60	-	nS	
Reverse Recovery Charge	Q _{rr}		-	106	-	nC	

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
3. Guaranteed by design, not subject to production
4. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=0.25mH, R_G=25\Omega$

Typical Electrical and Thermal Characteristics

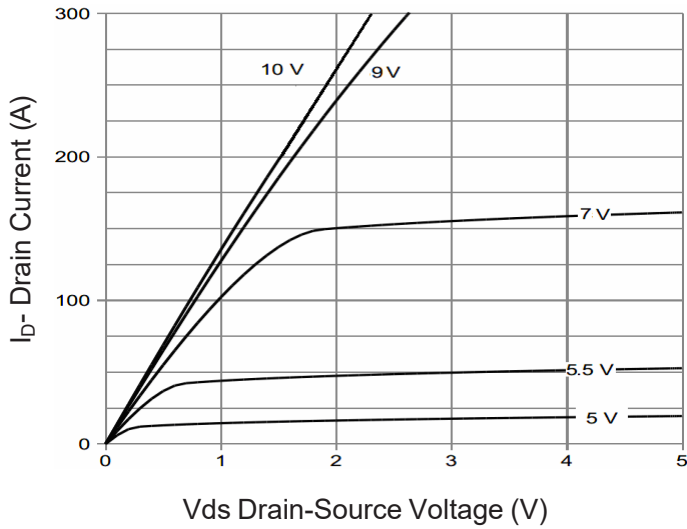


Figure 1 Output Characteristics

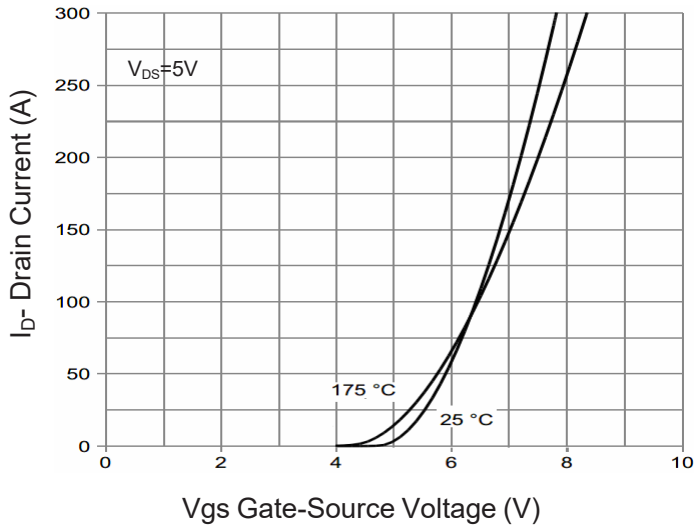


Figure 2 Transfer Characteristics

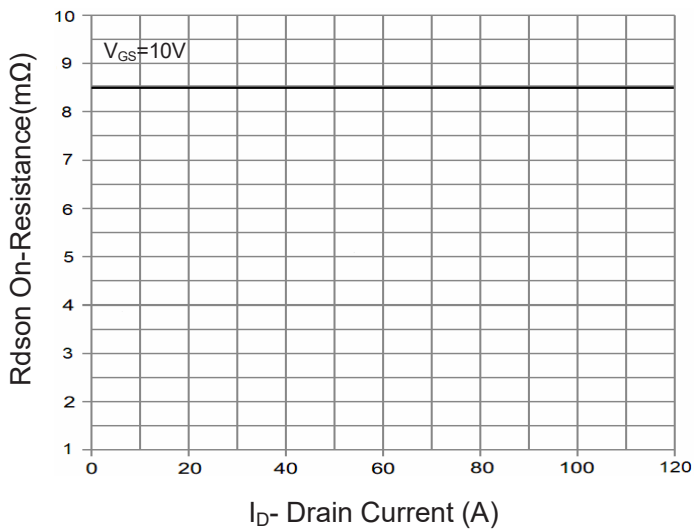


Figure 3 Rdson- Drain Current

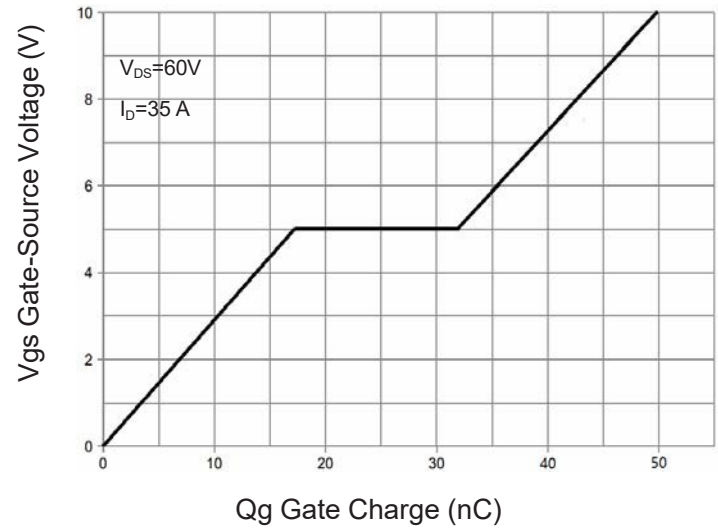


Figure 4 Gate Charge

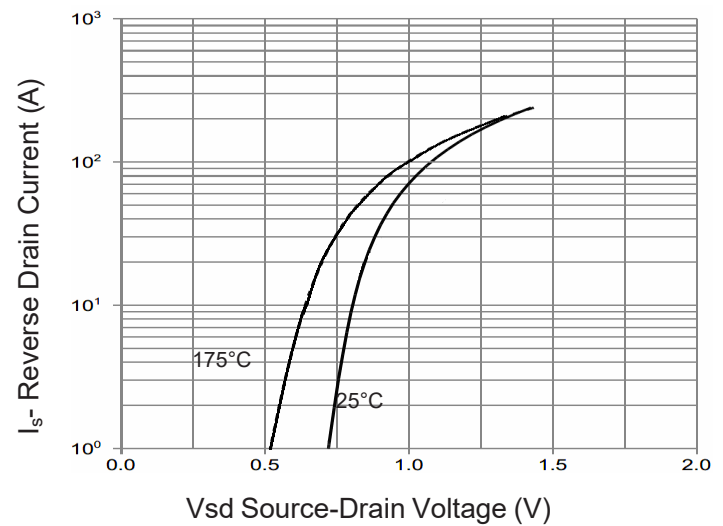


Figure 5 Source- Drain Diode Forward

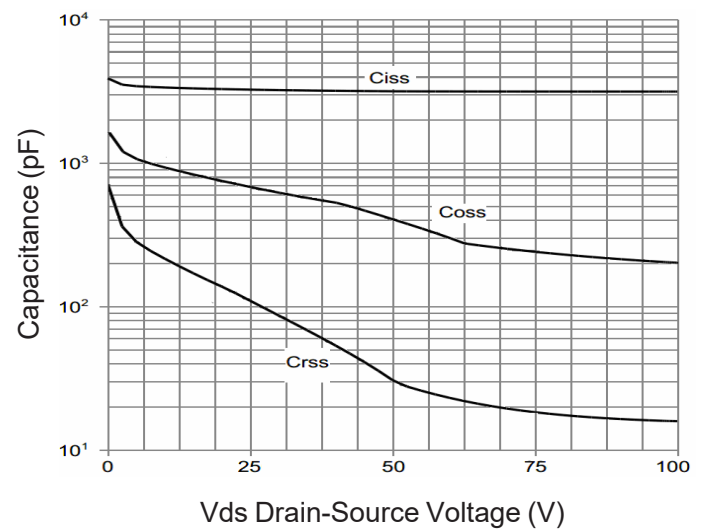
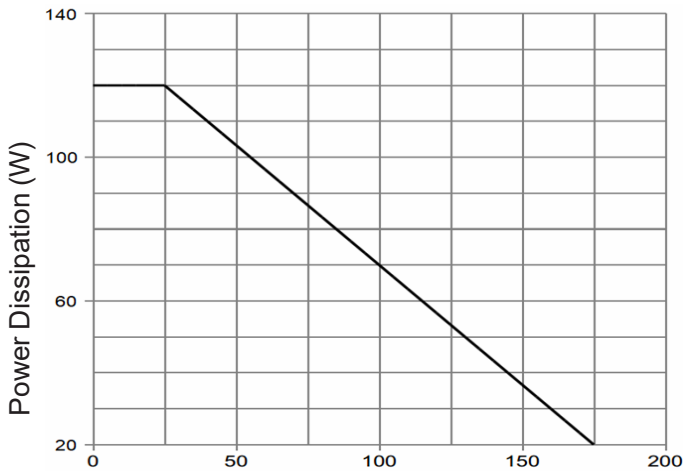
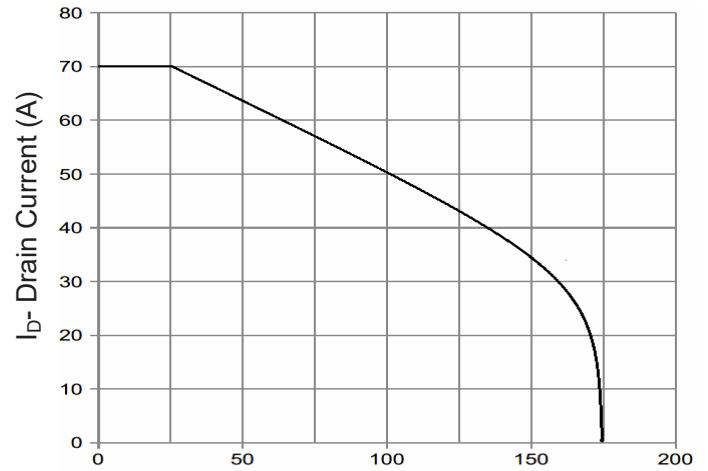


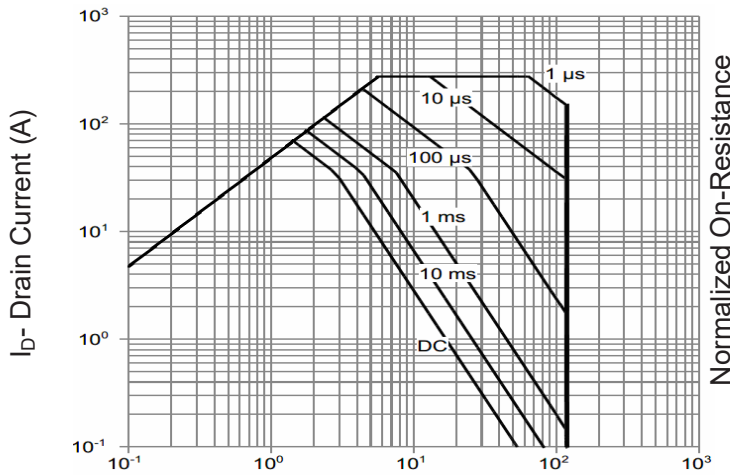
Figure 6 Capacitance vs Vds



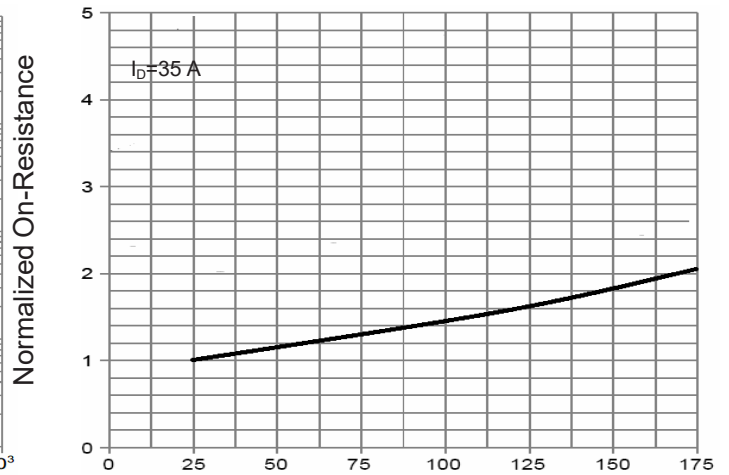
T_J -Junction Temperature(°C)
Figure 7 Power De-rating



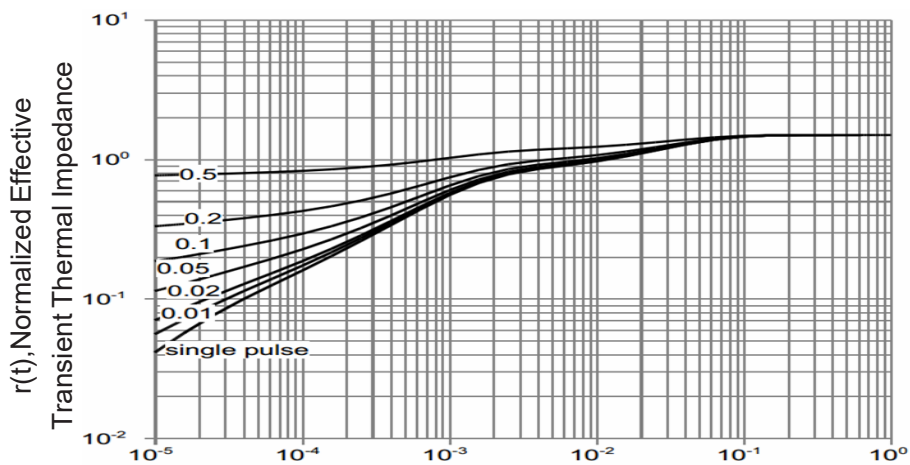
T_J -Junction Temperature (°C)
Figure 9 Current De-rating



V_{DS} Drain-Source Voltage (V)
Figure 8 Safe Operation Area



T_J -Junction Temperature(°C)
Figure 10 Rdson-Junction Temperature



Square Wave Pluse Duration(sec)
Figure 11 Normalized Maximum Transient Thermal Impedance